

July 2010

# **FDN8601**

# N-Channel PowerTrench<sup>®</sup> MOSFET 100 V, 2.7 A, 109 m $\Omega$

### **Features**

- Max  $r_{DS(on)}$  = 109 m $\Omega$  at  $V_{GS}$  = 10 V,  $I_D$  = 1.5 A
- Max  $r_{DS(on)}$  = 175 m $\Omega$  at  $V_{GS}$  = 6 V,  $I_D$  = 1.2 A
- High performance trench technology for extremely low r<sub>DS(on)</sub>
- High power and current handling capability in a widely used surface mount package
- Fast switching speed
- 100% UIL tested
- RoHS Compliant

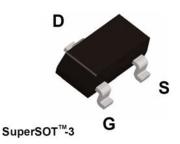


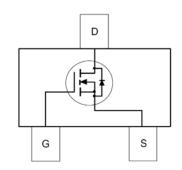
# **General Description**

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been optimized for  $r_{DS(on)}$ , switching performance and ruggedness.

# **Applications**

- Primary DC-DC Switch
- Load Switch





# MOSFET Maximum Ratings TA = 25 °C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DS</sub>	Drain to Source Voltage		100	V
V <sub>GS</sub>	Gate to Source Voltage		±20	V
1	-Continuous	(Note 1a)	2.7	^
ID	-Pulsed		12	- A
E <sub>AS</sub>	Single Pulse Avalanche Energy	(Note 3)	13	mJ
D	Power Dissipation	(Note 1a)	1.5	w
$P_{D}$	Power Dissipation	(Note 1b)	0.6	VV
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C

#### **Thermal Characteristics**

$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	75	°C/M
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	80	°C/W

## **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
8601	FDN8601	SSOT-3	7 "	8 mm	3000 units

# **Electrical Characteristics** $T_J = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, referenced to 25 °C		68		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V			1	μΑ
I <sub>GSS</sub>	Gate to Source Leakage Current	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V			±100	nA

#### On Characteristics (Note 2)

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	2.0	3.0	4.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, referenced to 25 °C		-8		mV/°C
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.5 A		85.4	109	
r <sub>DS(on)</sub>	Static Drain to Source On Resistance	$V_{GS} = 6 \text{ V}, I_D = 1.2 \text{ A}$		117	175	mΩ
, ,		$V_{GS} = 10 \text{ V}, I_D = 1.5 \text{ A}, T_J = 125 ^{\circ}\text{C}$		143	183	
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.5 A		8		S

#### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V 50.V.V 0.V	156	210	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 0 V, f = 1 MHz	47	65	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 = 1 WHZ	2.7	5	pF
$R_{a}$	Gate Resistance		1.0		Ω

## **Switching Characteristics**

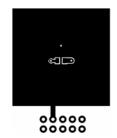
t <sub>d(on)</sub>	Turn-On Delay Time		4.3	10	ns
t <sub>r</sub>	Rise Time	V <sub>DD</sub> = 50 V, I <sub>D</sub> = 1.5 A,	1.3	10	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS}$ = 10 V, $R_{GEN}$ = 6 $\Omega$	7.8	16	ns
t <sub>f</sub>	Fall Time		3.4	10	ns
$Q_g$	Total Gate Charge	V <sub>GS</sub> = 0 V to 10 V	3	5	nC
Qg	Total Gate Charge	$V_{GS} = 0 \text{ V to 5 V}$ $V_{DD} = 50 \text{ V},$	1.8	3	nC
$Q_{gs}$	Gate to Source Gate Charge	I <sub>D</sub> = 1.5 A	0.9		nC
$Q_{gd}$	Gate to Drain "Miller" Charge		0.8		nC

#### **Drain-Source Diode Characteristics**

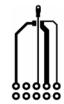
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 1.5 \text{ A}$ (Note 2)		0.81	1.3	V
t <sub>rr</sub>	Reverse Recovery Time	L = 1.5 A di/dt = 100 A/us		29	46	ns
Q <sub>rr</sub>	Reverse Recovery Charge	I <sub>F</sub> = 1.5 A, di/dt = 100 A/μs		15	27	nC

#### Notes

<sup>1.</sup> R<sub>0,1A</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>0,1C</sub> is guaranteed by design while R<sub>0CA</sub> is determined by the user's board design.



a) 80 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b) 180 °C/W when mounted on a minimum pad.

- 2. Pulse Test: Pulse Width < 300  $\mu\text{s},$  Duty cycle < 2.0%.
- 3. Starting T  $_{J}$  = 25 °C; N-ch: L = 3 mH, I  $_{AS}$  = 3 A, V  $_{DD}$  = 100 V, V  $_{GS}$  = 10 V.

# **Typical Characteristics** T<sub>J</sub> = 25 °C unless otherwise noted

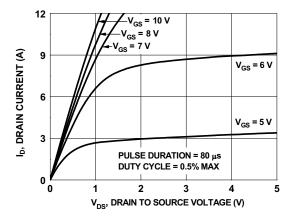


Figure 1. On-Region Characteristics

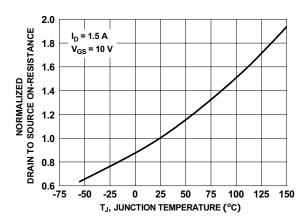


Figure 3. Normalized On-Resistance vs Junction Temperature

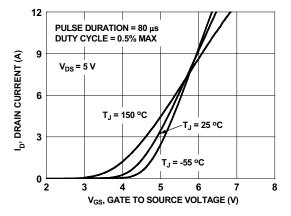


Figure 5. Transfer Characteristics

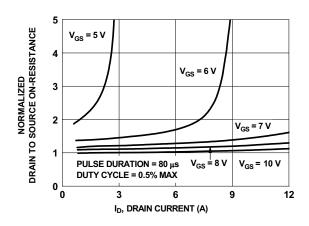


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

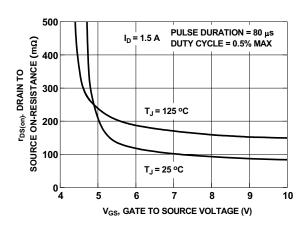


Figure 4. On-Resistance vs Gate to Source Voltage

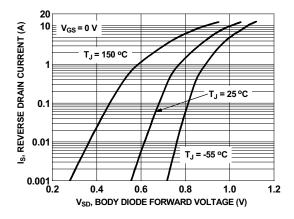


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

# Typical Characteristics T<sub>J</sub> = 25 °C unless otherwise noted

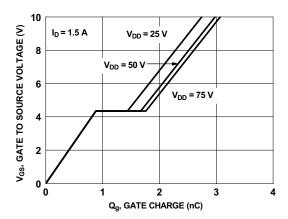


Figure 7. Gate Charge Characteristics

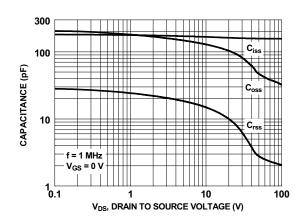


Figure 8. Capacitance vs Drain to Source Voltage

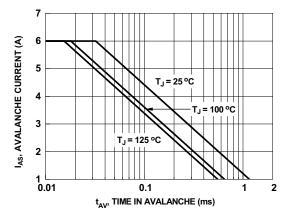


Figure 9. Unclamped Inductive Switching Capability

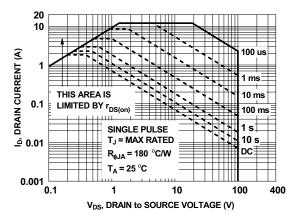


Figure 10. Forward Bias Safe Operating Area

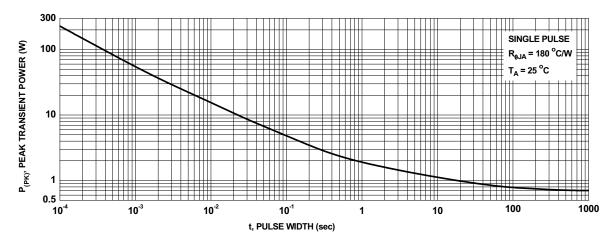


Figure 11. Single Pulse Maximum Power Dissipation

# **Typical Characteristics** T<sub>J</sub> = 25 °C unless otherwise noted

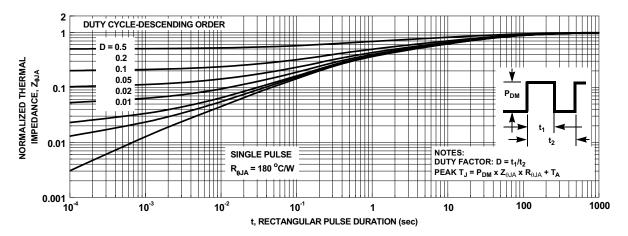


Figure 12. Junction-to-Ambient Transient Thermal Response Curve





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